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B<sup>2</sup>  
In the pixel portion 188, a gate wiring 189 extending from the scanning signal driver circuit 185 and a source wiring 190 extending from the image signal driver circuit 186a intersect into a matrix shape to form pixels. Each pixel is provided with a pixel TFT 204 and a storage capacitor 205 as shown in Figure 6A.

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Sub C1  
B<sup>3</sup>  
Thereafter, a resist mask having a predetermined pattern is formed by using a photomask PM5 (Fig. 6A). Contact holes reaching the source or drain regions of the respective island-like semiconductor films are formed in the insulating films 138 and 139. Further, insulating film 138 and 139 are removed from the terminal section 182. The contact holes are formed by dry etching. In this case, a mixed gas of CF<sub>4</sub>O<sub>2</sub> and He is used as the etching gas. The interlayer insulating film 139 formed of the organic resin material is first etched. Then, the etching gas is switched to CF<sub>4</sub>O<sub>2</sub> and the protective insulating film 138 is etched. To improve the selection ratio with the island-like semiconductor films, the etching gas is switched further to CHF<sub>3</sub> and the gate insulating film is etched. In this way, the contact holes can be formed satisfactory.

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B<sup>4</sup>  
Further in this embodiment columnar spacer 172 is formed, as shown in Fig. 7, on the active matrix substrate which went through the above described processes. At the same time, a protective film 173 which protects side face of the terminal section 182 of the connection wiring 183 is formed with the formation of the columnar spacer 172. The material of the columnar spacer 172 is not limited, in particular, and they may be formed by using, for example, "NN700" of JSR Co., and after the material is coated by a spinner, a prescribed pattern is formed by exposure and development. The pattern is then heated and cured at 150 to 200° C in a clean oven. Or like the like.